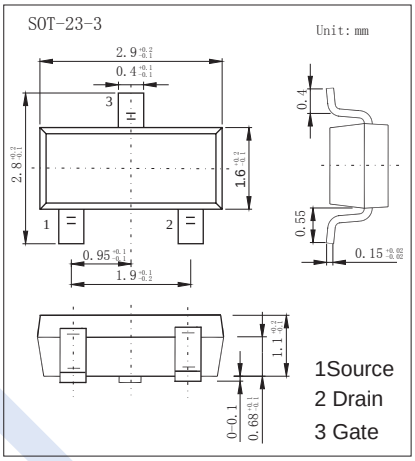
N-Channel Junction Silicon FET
2SK303



Features

- Ideal for potentiometers, analog switches, low frequency amplifiers, constant current supplies, and impedance conversion.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to Drain voltage	V_{GDS}	-30	V
Gate current	I_G	10	m A
Drain current	I_D	20	m A
Power dissipation	P_D	200	mW
Channel temperature	T_{ch}	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

* PW≤10 us,Duty Cycle≤1%

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Gate to drain	V_{GDS}	I_G=-10 μ A	-30			V
Gate to source leakage current	I_{GSS}	V_{GS}=-20V			-1.0	nA
Drain cut-off current	I_{DSS}	V_{DS}=10V,V_{GS}=0	0.6		12.0	mA
Cutoff voltage	$V_{GS(off)}$	V_{DS}=10V,I_D=1 μ A		-1	-4	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS}=10V,V_{GS}=0,f=1K Hz	2.5	6.0		ms
Drain to source on-state resistance	$R_{DS(on)}$	V_{GS}=0,V_{DS}=10mV		250		Ω
Input capacitance	C_{iss}	V_{DS}=10V,V_{GS}=0,f=1MHZ		5		pF
Reverse transfer capacitance	C_{rss}			1.5		pF

I_{DSS} Classification unit:mA

Marking	V2	V3	V4	V5
Rank	2	3	4	5
I_{DSS}	0.6～1.5	1.2～3	2.5～6	5～12

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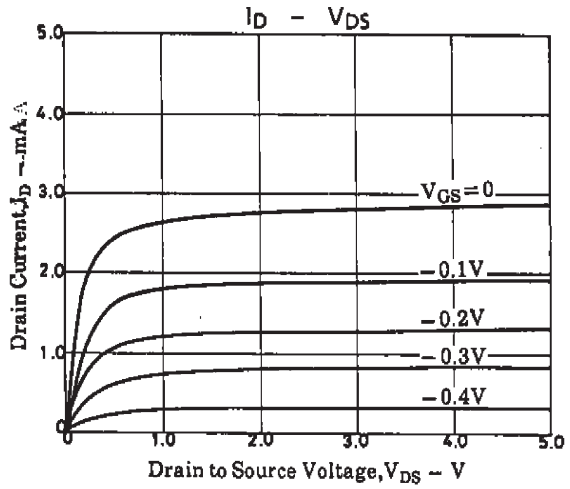
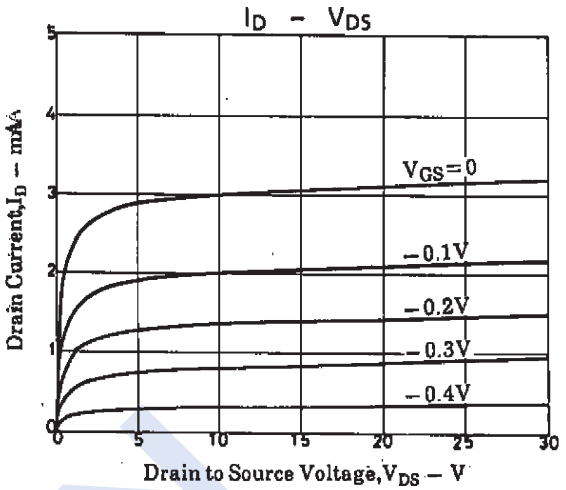
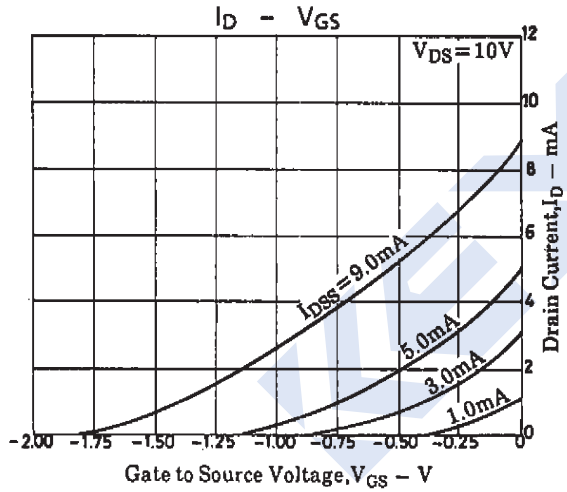
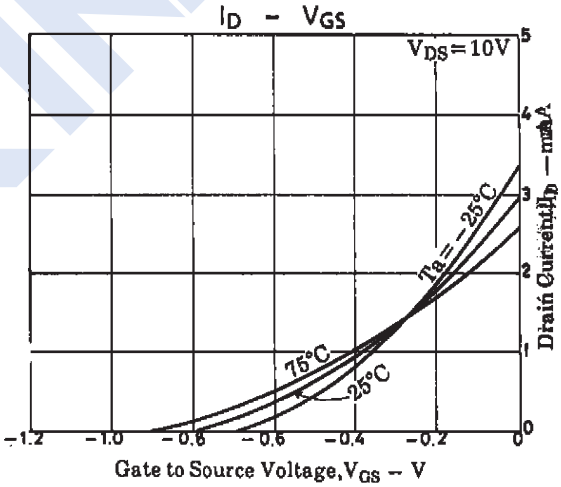
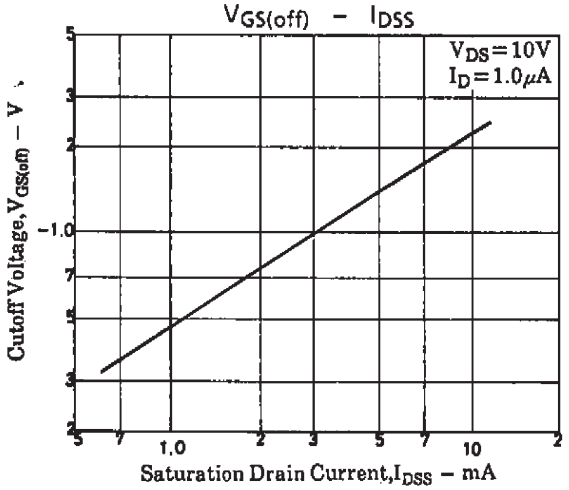
■ Typical Characterisitics

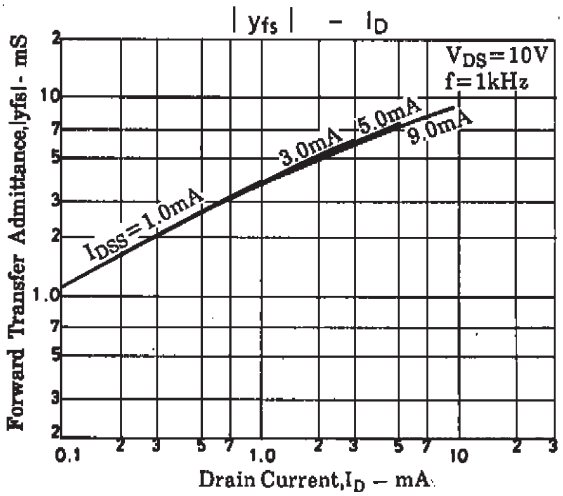












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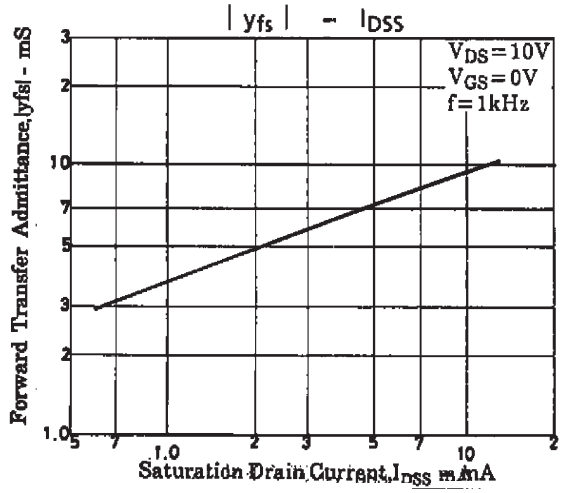

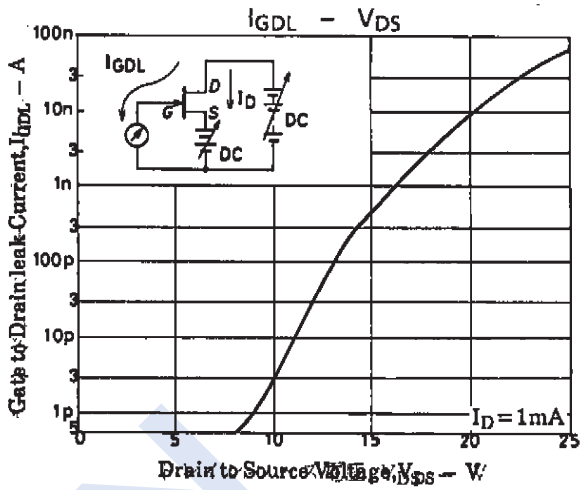

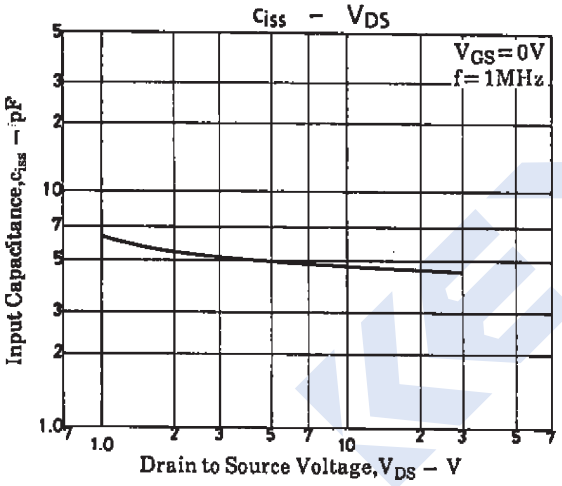

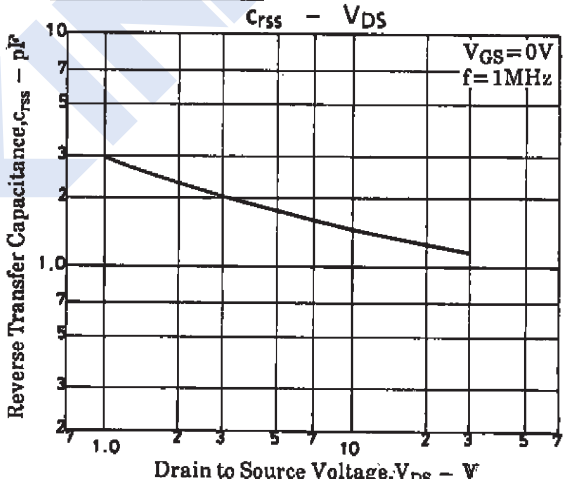

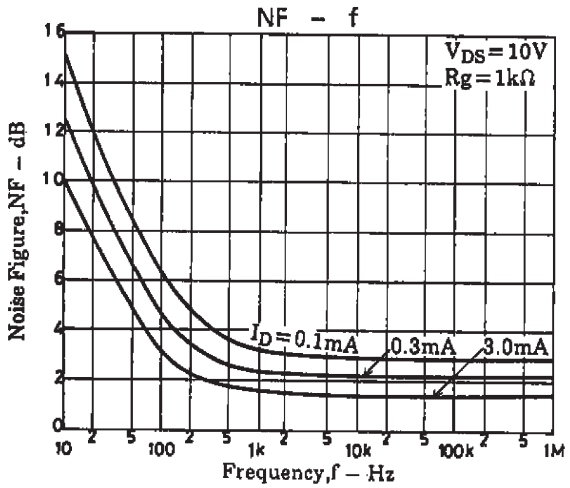

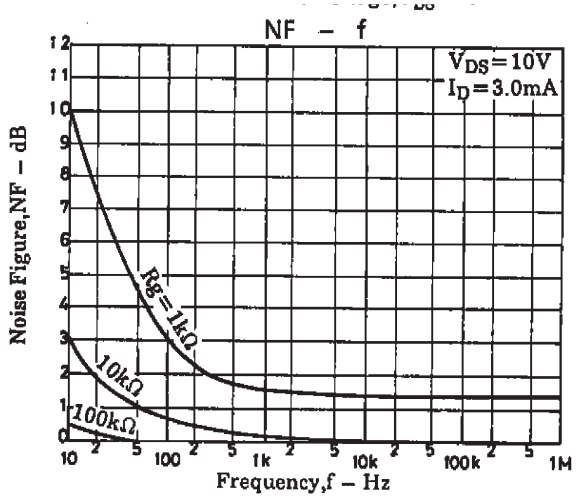

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